

**AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) A manufacturing method of an SOI wafer, comprising:  
preparing a supporting wafer comprising boron in an amount of  $9 \times 10^{18}$  atoms/cm<sup>3</sup> or more;  
~~forming a rear surface an insulating film having a thickness of 0.1-0.5 μm on at least a surface opposite to a bonding surface on one surface of said supporting wafer;~~  
ion-implanting hydrogen gas or a noble gas element to an active layer wafer to thereby form an ion-implanted layer in said active layer wafer;  
bonding said active layer wafer with ~~a~~ the other surface of said supporting wafer via an insulating film interposed therebetween to thereby form a bonded wafer; and then heat treating said bonded wafer to thereby induce cleavage in a portion of said bonded wafer at the site of the ion-implanted layer as an interface to thereby form an SOI layer with said remaining active layer wafer for manufacturing said SOI wafer.

2. (Cancelled)

3. (Previously Presented) A manufacturing method of an SOI wafer in accordance with claim 1, wherein a thickness of the SOI layer is less than 0.10 μm.

- 4 - 21. (Cancelled)